

March 2008

FDG6342L

Integrated Load Switch

Features

- Max $r_{DS(on)} = 150 m\Omega$ at $V_{GS} = 4.5 V$, $I_D = -1.5 A$
- Max $r_{DS(on)} = 195m\Omega$ at $V_{GS} = 2.5V$, $I_D = -1.3A$
- Max $r_{DS(on)} = 280 \text{m}\Omega$ at $V_{GS} = 1.8 \text{V}$, $I_D = -1.1 \text{A}$
- Max $r_{DS(on)} = 480 \text{m}\Omega$ at $V_{GS} = 1.5 \text{V}$, $I_D = -0.9 \text{A}$
- Control MOSFET (Q1) includes Zener protection for ESD ruggedness (>4KV Human body model)
- High performance trench technology for extremely low r_{DS(on)}
- Compact industry standard SC70-6 surface mount package
- RoHS Compliant

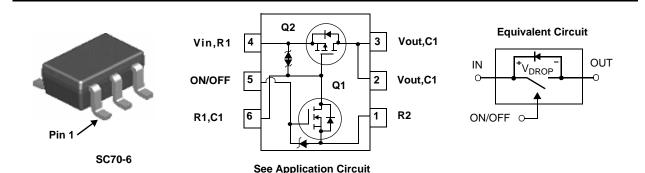


General Description

This device is particularly suited for compact power management in portable electronic equipment where 2.5V to 8V input and 1.5A output current capability are needed. This load switch integrates a small N-Channel power MOSFET (Q1) that drives a large P-Channel power MOSFET (Q2) in one tiny SC70-6 package.

Applications

- Power management
- Load switch



MOSFET Maximum Ratings T_A = 25℃ unless otherwise noted

Symbol	Parameter	Ratings	Units	
V _{IN}	Gate to Source Voltage (Q2)		±8	V
V _{ON/OFF}	Gate to Source Voltage (Q1)		-0.5 to 8	V
I _{Load}	Load Current -Continuous	(Note 2)	-1.5	
	-Pulsed	(Note 2)	-6	A
Б	Power Dissipation for Single Operation	(Note 1a)	0.36	10/
P_D		(Note 1b)	0.3	W
T _J , T _{STG}	Operating and Storage Junction Temperature Range		-55 to +150	${\mathcal C}$

Thermal Characteristics

$R_{\theta JA}$	Thermal Resistance, Junction to Ambient Single operation	(Note 1a)	350	C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient Single operation	(Note 1b)	415	C/VV

Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
.2L	FDG6342L	SC70-6	7"	8mm	3000units

Electrical Characteristics $T_J = 25$ $^{\circ}$ C unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Тур	Max	Units
Off Chara	cteristics					
BV_{IN}	V _{IN} Breakdown Voltage	$I_D = -250 \mu A, V_{ON/OFF} = 0 V$	8			V
I _{Load}	Zero Gate Voltage Drain Current	$V_{IN} = -6.4V$, $V_{ON/OFF} = 0V$			-1	μΑ
I _{FL}	Leakage Current, Forward	V _{IN} = 8V, V _{ON/OFF} = 0V			10	μΑ
I _{RL}	Leakage Current, Reverse	$V_{IN} = -8V$, $V_{ON/OFF} = 0V$			-10	μΑ

On Characteristics (note 2)

V _{ON/OFF(th)}	Gate Threshold Voltage	$V_{IN} = V_{ON/OFF}, I_D = -250\mu A$	0.65	0.8	1.5	V
	I Static Drain to Source On Resistance (O2)	$V_{IN} = 4.5V, I_D = -1.5A$		125	150	- mΩ - Ω
		$V_{IN} = 2.5V, I_D = -1.3A$		150	195	
r _{DS(on)}		$V_{IN} = 1.8V, I_D = -1.1A$		200	280	
		$V_{IN} = 1.5V, I_D = -0.9A$		250	480	
	Static Drain to Source On Resistance (OT)	$V_{IN} = 4.5V, I_D = 0.4A$		2.6	4.0	
		$V_{IN} = 2.7V, I_D = 0.2A$		3.3	5.0	22

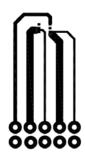
Drain-Source Diode Characteristics

I;	S	Maximum Continuous Drain to Source Diode Forward Current			-0.25	V
١	/ _{SD}	Source to Drain Diode Forward Voltage	$V_{ON/OFF} = 0V$, $I_S = -0.25A$ (Note 2)	-0.6	-1.2	V

1. $R_{\theta JA}$ is determined with the device mounted on a 1in² pad 2 oz copper pad on a 1.5 x 1.5 in. board of FR-4 material. $R_{\theta JC}$ is guaranteed by design while $R_{\theta JA}$ is determined by the user's board design.



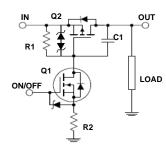
a. 350℃/W when mounted on a 1 in² pad of 2 oz copper.



b. 415℃/W when mounted on a minimum pad of 2 oz copper.

2. Pulse Test: Pulse Width < 300μ s, Duty cycle < 2.0%.

FDG6342LLoad Switch Application circuit



External Component Recommendation:

For additional in-rush current control, R2 and C1 can be added. For more information, see application note AN1030

Typical Characteristics T_J = 25℃ unless otherwise noted

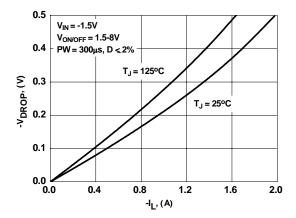


Figure 1. Conduction Voltage Drop Variation with Load Current.

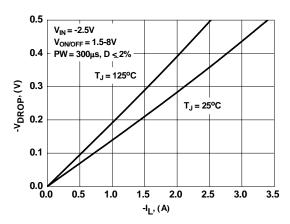


Figure 3. Conduction Voltage Drop Variation with Load Current.

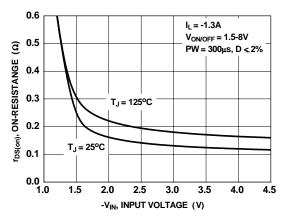


Figure 5. On-Resistance Variation With Input Voltage

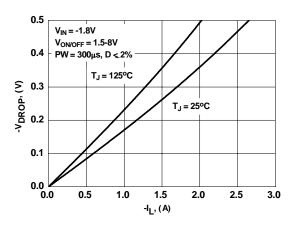


Figure 2. Conduction Voltage Drop Variation with Load Current.

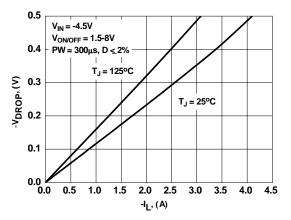


Figure 4. Conduction Voltage Drop Variation with Load Current.

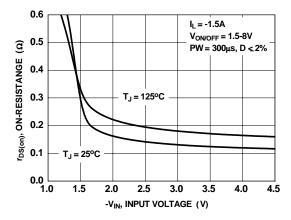


Figure 6. On-Resistance Variation With Input Voltage





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